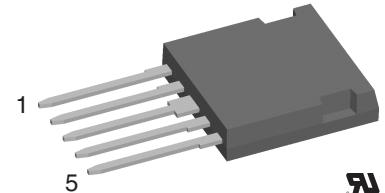
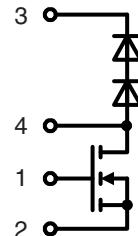


**HiPerFET™**  
**CoolMOS™<sup>1)</sup> Power MOSFETs**  
-Boost Chopper Topology-  
in ISOPLUS i4-PAC™

**I<sub>D25</sub> = 38 A**  
**V<sub>DSS</sub> = 600 V**  
**R<sub>DSon</sub> = 60 mΩ**



**MOSFET**

Symbol	Conditions	Maximum Ratings		
V <sub>DSS</sub>	T <sub>VJ</sub> = 25°C to 150°C	600		V
V <sub>GS</sub>		±20		V
I <sub>D25</sub>	T <sub>C</sub> = 25°C	38		A
I <sub>D90</sub>	T <sub>C</sub> = 90°C	25		A

Symbol	Conditions	Characteristic Values		
		(T <sub>VJ</sub> = 25°C, unless otherwise specified)	min.	typ.
R <sub>DSon</sub>	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 20 A		60	70 mΩ
V <sub>Gsth</sub>	V <sub>DS</sub> = 20 V; I <sub>D</sub> = 2.7 mA	2.1		3.9 V
I <sub>DSS</sub>	V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0 V; T <sub>VJ</sub> = 25°C T <sub>VJ</sub> = 125°C		250	25 μA μA
I <sub>GSS</sub>	V <sub>GS</sub> = ±20 V; V <sub>DS</sub> = 0 V			200 nA
Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub>	{ V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 350 V; I <sub>D</sub> = 47 A		250 25 120	nC nC nC
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub>	{ V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 380 V; I <sub>D</sub> = 47 A; R <sub>G</sub> = 1.8 Ω		20 30 110 10	ns ns ns ns
V <sub>F</sub>	(reverse conduction) I <sub>F</sub> = 20 A; V <sub>GS</sub> = 0 V	0.9		V
R <sub>thJC</sub> R <sub>thJS</sub>		tbd	0.45 K/W K/W	

**Features**

- fast CoolMOS™<sup>1)</sup> power MOSFET  
3rd generation
  - high blocking voltage
  - low on resistance
  - low thermal resistance due to reduced chip thickness
- HiPerDyn™ FRED
  - consisting of series connected diodes
  - enhanced dynamic behaviour for high frequency operation
- ISOPLUS i4-PAC™ package
  - isolated back surface
  - low coupling capacity between pins and heatsink
  - enlarged creepage towards heatsink
  - application friendly pinout
  - low inductive current path
  - high reliability
  - industry standard outline
  - UL registered, E 72873

**Applications**

- chopper for power factor correction
- supply of high frequency transformer
  - switched mode power supplies
  - welding converters

<sup>1)</sup> CoolMOS™ is a trademark of Infineon Technologies AG.

**Free Wheeling Diode (data for series connection)**

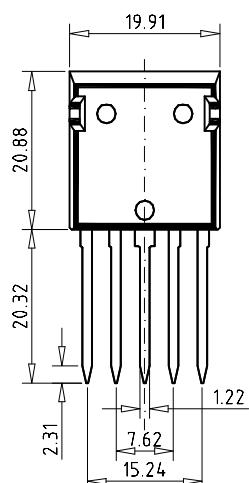
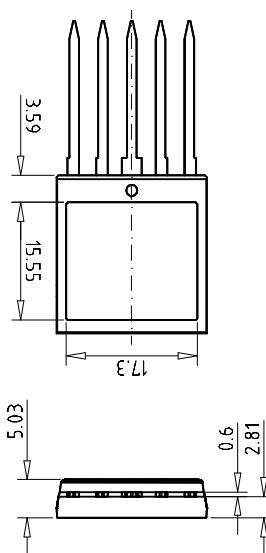
Symbol	Conditions	Maximum Ratings		
$V_{RRM}$	$T_{VJ} = 25^\circ\text{C}$ to $150^\circ\text{C}$	600		V
$I_{F25}$	$T_c = 25^\circ\text{C}$	80		A
$I_{F90}$	$T_c = 90^\circ\text{C}$	45		A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$V_F$	$I_F = 20 \text{ A}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.6 2.0	2.9 V	V
$I_R$	$V_R = V_{RRM}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	0.25	0.25 mA mA	
$I_{RM}$ $t_{rr}$	$\left. \begin{array}{l} I_F = 30 \text{ A}; dI_F/dt = -500 \text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C} \\ V_R = 300 \text{ V} \end{array} \right\}$	9 40		A ns
$R_{thJC}$ $R_{thJS}$	(per diode)	tbd	0.65 K/W K/W	

**Component**

Symbol	Conditions	Maximum Ratings	
$T_{VJ}$		-55...+150	°C
$T_{stg}$		-55...+125	°C
$V_{ISOL}$	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$	2500	V~
$F_c$	mounting force with clip	20...120	N

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$C_p$	coupling capacity between shorted pins and mounting tab in the case	40		pF
$d_s, d_A$	pin - pin	1.7		mm
$d_s, d_A$	pin - backside metal	5.5		mm
<b>Weight</b>		9		g

**Dimensions in mm (1 mm = 0.0394")**

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